

L Number	Hits	Search Text	DB	Time stamp
1	6	((("5753554") or ("6368920") or ("6307231")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 13:42
2	7598	257/244,283,284,301-305,330-334,618-628.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 13:47
3	41	257/244,283,284,301-305,330-334,618-628.ccls. and (MISFET with (groove trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:19
4	3	("4689871"   "4954854"   "5122848").PN.	USPAT	2004/06/23 14:00
5	8	("5366914"   "5479037"   "5558313"   "5578508"   "5907776"   "5918114"   "5940721"   "5981344").PN.	USPAT	2004/06/23 14:01
6	6	("4742015"   "5135880"   "5248627"   "5527720"   "5567634"   "5648288").PN.	USPAT	2004/06/23 14:03
7	10	("4573066"   "4707719"   "4774560"   "4914058"   "4931846"   "4983535"   "5072266"   "5160491"   "5387528"   "5405794").PN.	USPAT	2004/06/23 14:04
8	11	("4573066"   "4707719"   "4774560"   "4830981"   "4904613"   "4914058"   "4920064"   "4983535"   "5072266"   "5160491"   "5242845").PN.	USPAT	2004/06/23 14:06
9	9	("4653177"   "4893160"   "4994409"   "5029324"   "5034785"   "5047359"   "5126807"   "5168331"   "5364810").PN.	USPAT	2004/06/23 14:08
10	3	("5023196"   "5128278"   "5182222").PN.	USPAT	2004/06/23 14:10
11	6	("4333794"   "4381953"   "4385975"   "4569701"   "4582565"   "4593459").PN.	USPAT	2004/06/23 14:13
12	2	("5918114").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:18
13	2	("4685196"   "5362665").PN.	USPAT	2004/06/23 14:16
14	6	("4689871"   "4829017"   "4891327"   "5192704"   "5244824"   "5270239").PN.	USPAT	2004/06/23 14:17
15	346097	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:19
16	245	(257/\$.ccls. 438/\$.ccls.) and (MISFET with (groove trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 14:20
17	15	("3975221"   "4003126"   "4084175"   "4272302"   "5258332"   "5693569"   "5733810"   "5744826"   "5753554"   "5783491"   "5817558"   "6307231"   "6368920"   "6455378"   "6511886").PN.	USPAT	2004/06/23 14:33
18	3	("4992390"   "5473176"   "6198127").PN.	USPAT	2004/06/23 14:34
19	15	("4546367"   "4589193"   "4767722"   "4921815"   "4941026"   "4992838"   "5016068"   "5040034"   "5196373"   "5248894"   "5321289"   "5385853"   "5410170"   "5468982"   "5726088").PN.	USPAT	2004/06/23 14:34
20	10	("4830975"   "4939100"   "4959326"   "5155053"   "5405787"   "5552329"   "5580803"   "5688704"   "5698461"   "5736435").PN.	USPAT	2004/06/23 14:37
21	13	("4666556"   "4835585"   "5237187"   "5612557"   "5621232"   "5717254"   "5734175"   "5972768"   "6008114"   "6107196"   "6406998"   "6472317"   "6482735").PN.	USPAT	2004/06/23 14:40
22	1	"4353086".PN.	USPAT	2004/06/23 14:49

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1	303	(257/\$.ccls. 438/\$.ccls.) and (MISFET with MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:17
2	3	((257/\$.ccls. 438/\$.ccls.) and (MISFET with MOSFET)) and ((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:21
3	256	((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:22
4	0	((gate near (wir\$3 electrode contact)) near2 outside near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:31
5	13	((gate near (wir\$3 electrode contact)) near2 (trench groove) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07
6	0	((gate near (wir\$3 electrode contact)) near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:05
7	0	gate near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
8	0	((gate near (wir\$3 electrode contact)) with (form\$3 near on) with ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
9	0	((gate near (wir\$3 electrode contact)) same (form\$3 near on) same ((insulat\$3 dielectric) near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 17:30
10	22	(gate near (wir\$3 electrode contact)) near2 outside near2 (trench groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:03
11	25	((gate metal) near (wir\$3 electrode contact)) near2 outside near2 (trench groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:04
12	0	(wir\$3 electrode contact) near2 (form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07

13	0	(form\$3 near on) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06
14	0	(form\$3 near on) near ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:06
15	42552	(wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:07
16	908	((wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:09
17	15543	(gate conduct\$3 metal) near (wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
18	721	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 form\$3 near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
19	27941	(gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
20	1303	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:10
21	846	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source with drain with (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:11
22	513	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source near3 drain near3 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:12
23	300	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and (source near2 drain near2 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:12
24	176	((gate conduct\$3 metal) near (wir\$3 electrode contact) near2 ((insulat\$3 dielectric) near (layer film))) and MISFET and ((source near (layer region)) near2 (drain near (layer region)) near2 (base channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 18:13